

Design of a Prototype Frontend and Bias Generator for a new Readout Chip for LHCb

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Readout Chip for LHCb:

Silicon Vertex Detector

Inner Tracker

Pile-Up Veto Trigger

RICH (Multi Anode Photo multiplier tube or Pad Hybrid Photo Diode)

- chosen technology: standard 0.25um CMOS process
- 128 channels with analog input stages / 50um overall pitch
- capacitor array used as analogue pipeline
- 3 readout modes: 40 MHz via 4 ports analog } readout per event
80 MHz via 2 ports binary } < 900 ns
40 MHz via 1 port + daisy chaining
- fast trigger output via adjustable comparator threshold
- programmable latency up to 160 clock cycles
- 16 multi event buffer
- I2C programming interface
- intensive test and monitoring facilities

Requirements on radiation hardness (driven by vertex detector)

vertex detector FE-electronics:

2 MRad / year -> 10 MRad total dose

Design techniques to enhance radiation resistance:

- minimize threshold voltage shift by choice of technology
- edgeless n-mos transistor layout to reduce leakage current
- systematic use of guardrings to minimize SEE rate

*(Total Dose and Single Event Effects (SEE) in a 0.25um CMOS Technology,
F.Faccio et al. in CERN/LHCC/98-36)*

- forced bias currents / node voltages not fixed
- passive components used as negative feedback

(e.g. RD20 or HELIX128, W. Fallot-Burghardt et al. in HD-ASIC-33-0697)

Noise of the Frontend:

- noise of frontend determined by noise of input transistor

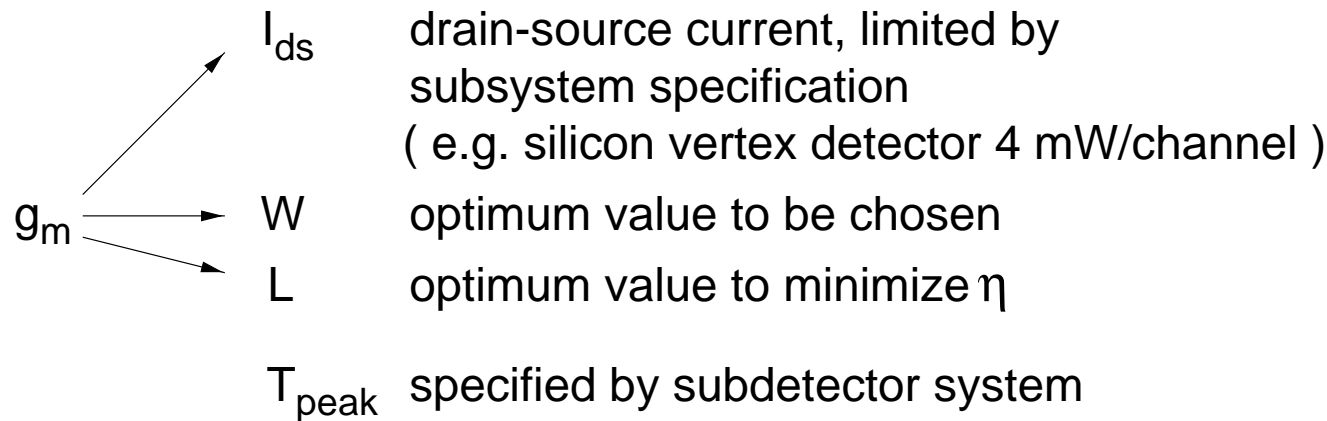
$$\frac{ENC_{thermal}}{C_{input}} = e \sqrt{\frac{(1 + \eta) \cdot kT}{3 \cdot T_{peak} \cdot g_m}}$$

- g_m transconductance of input transistor
- T_{peak} peaking time
- η bulk-source transconductance
(1/f noise can be neglected)

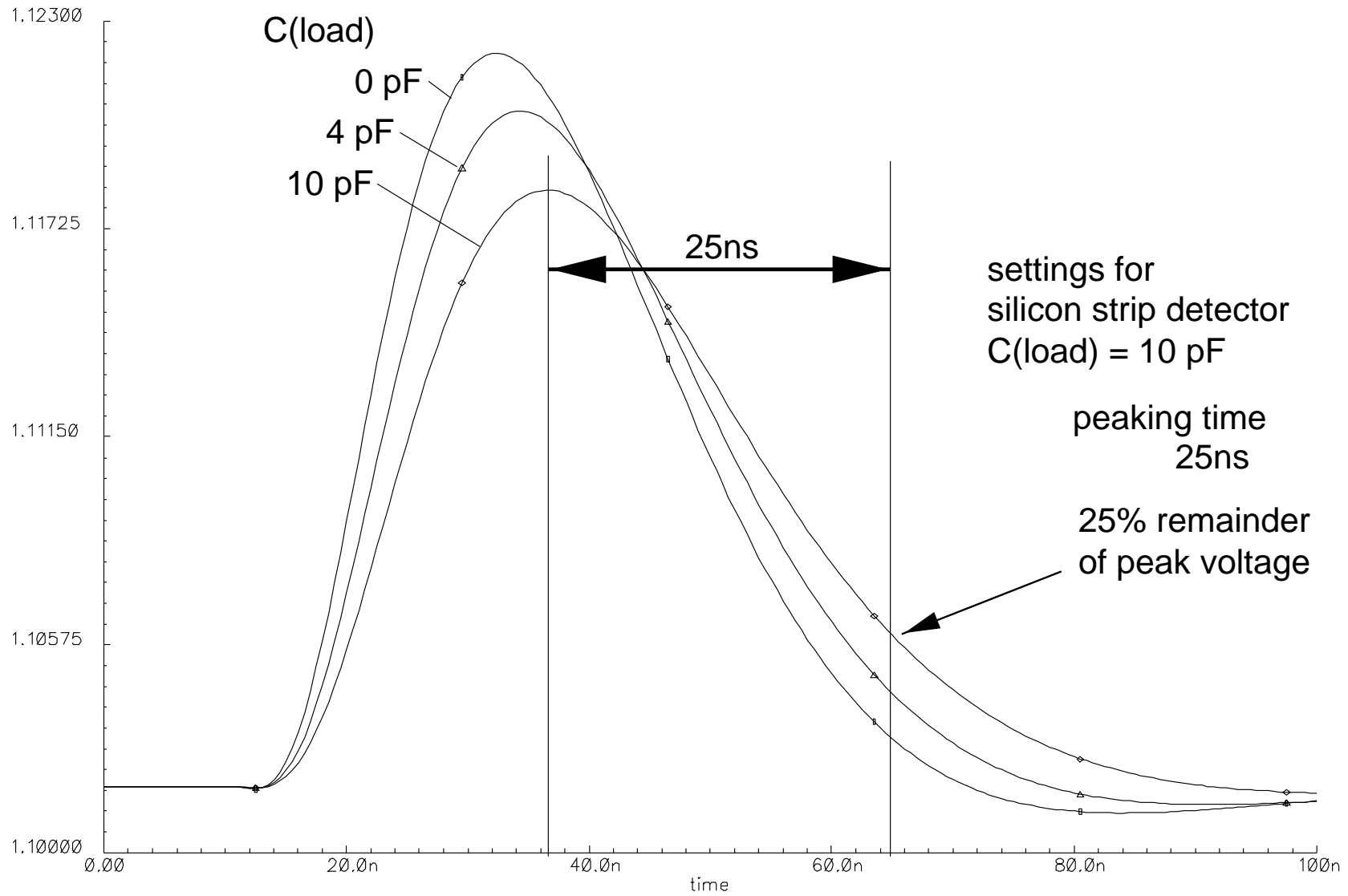
values simulated for third set

slope of noise function	power per channel
46.5 e/pF	0.88 mW
41.4 e/pF	1.13 mW
37.5 e/pF	1.38 mW
35.5 e/pF	1.63 mW
33.6 e/pF	1.88 mW

degrees of freedom:

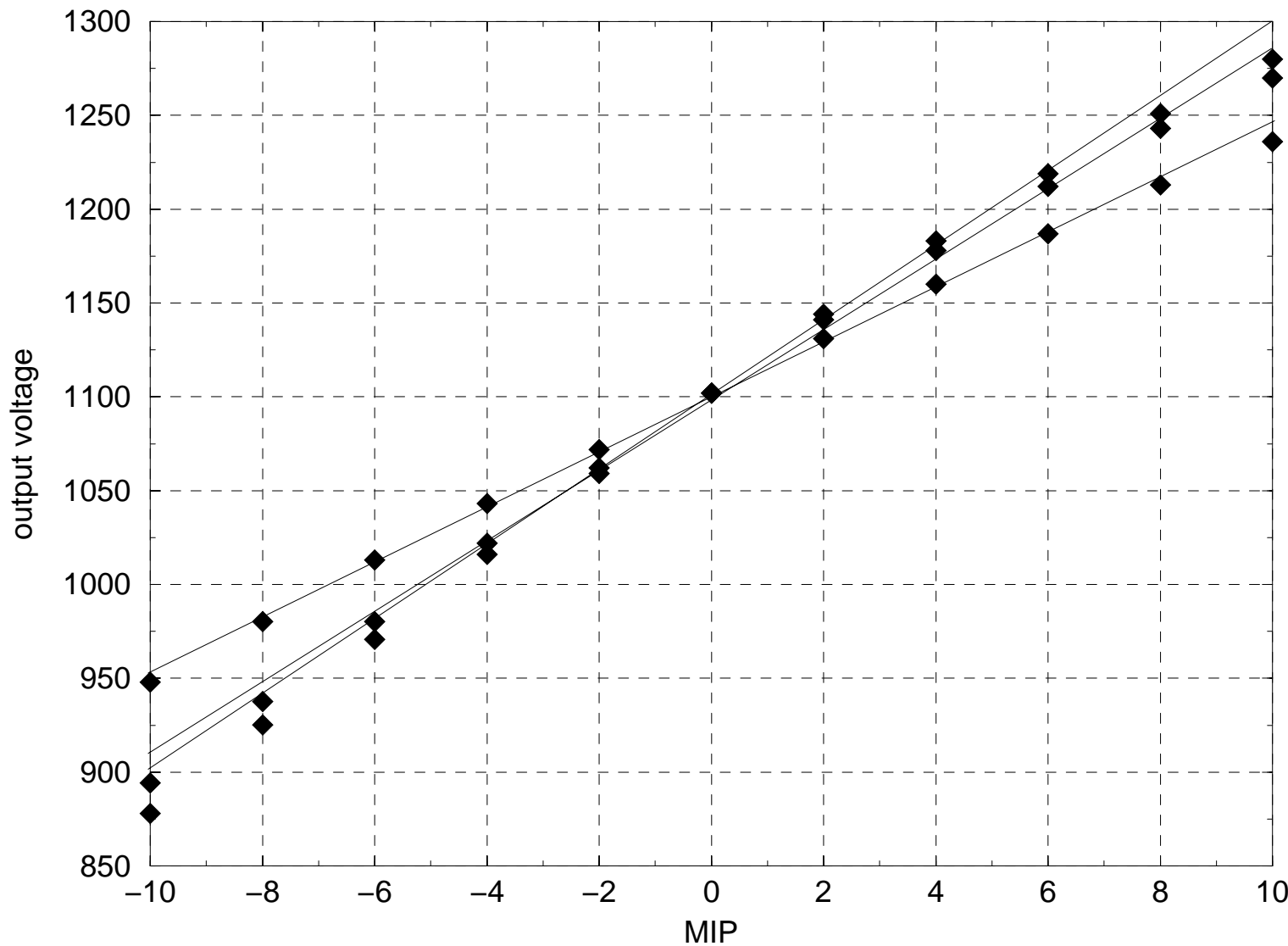


Simulation Results



Peak Voltage vs. Input Charge

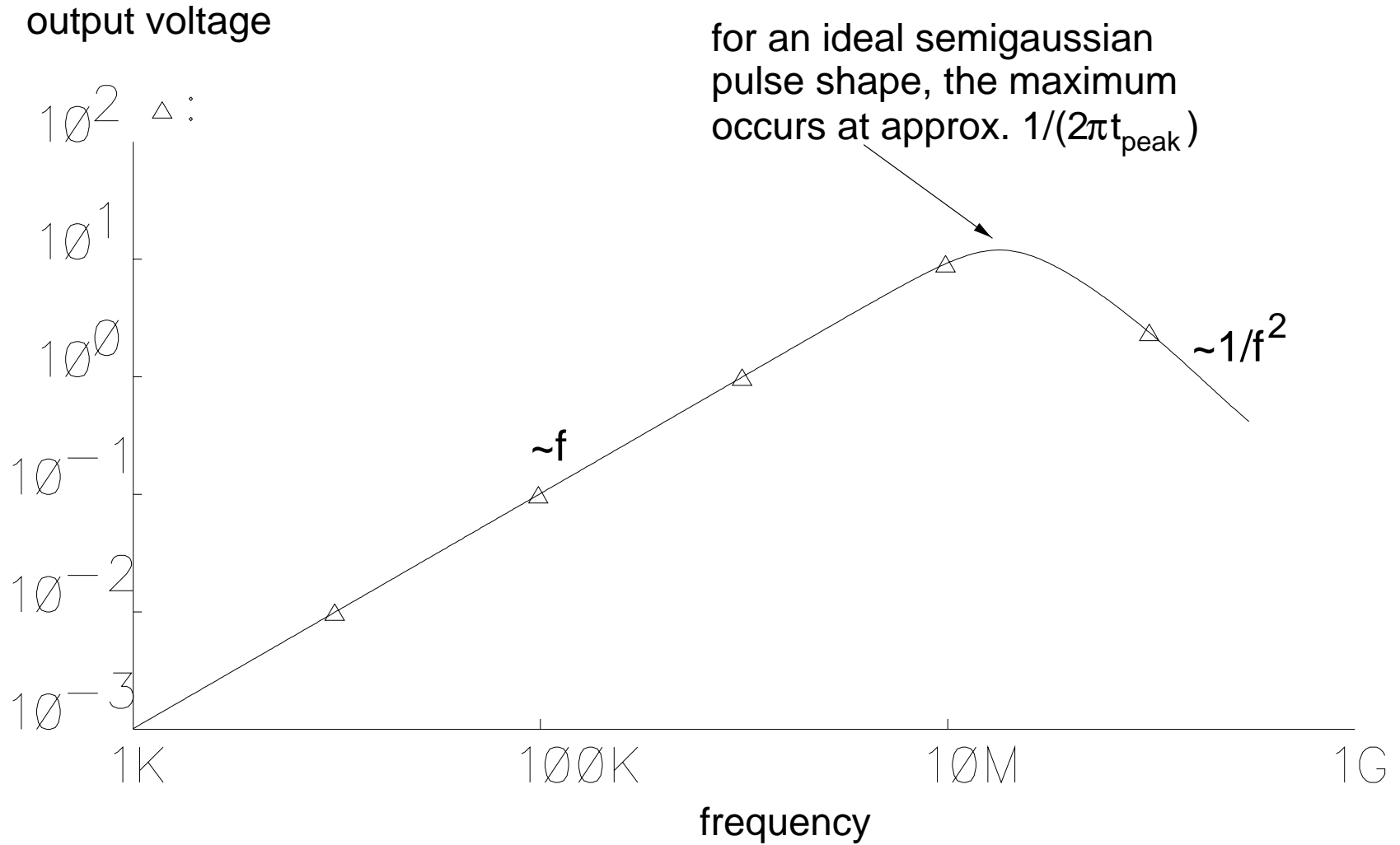
1 MIP = 11.000 electrons

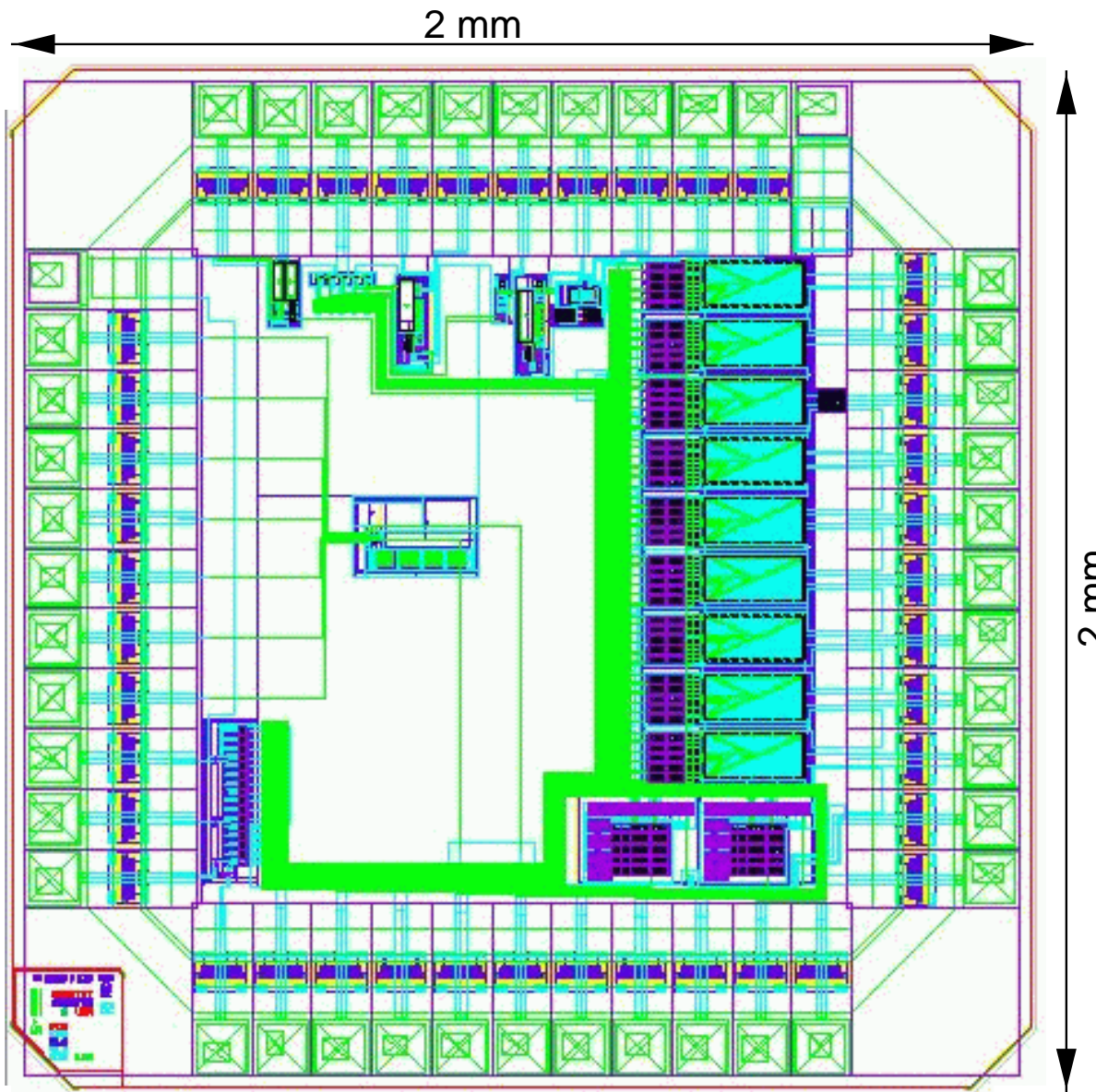


Simulated
dynamic range
-10 MIP to +10 MIP

load capacitance	gain
0pF	20.4 mV/MIP
4pF	19.0 mV/MIP
10pF	14.5 mV/MIP

Frequency response of the pulse shaper





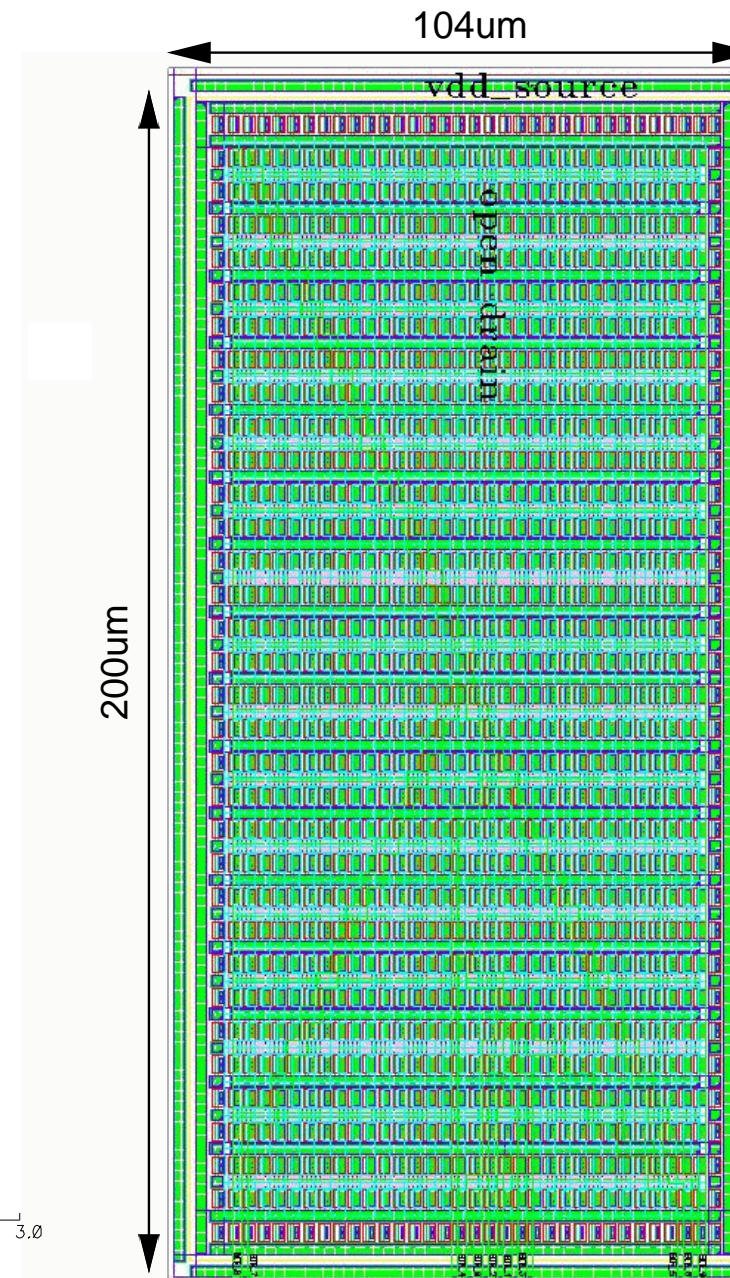
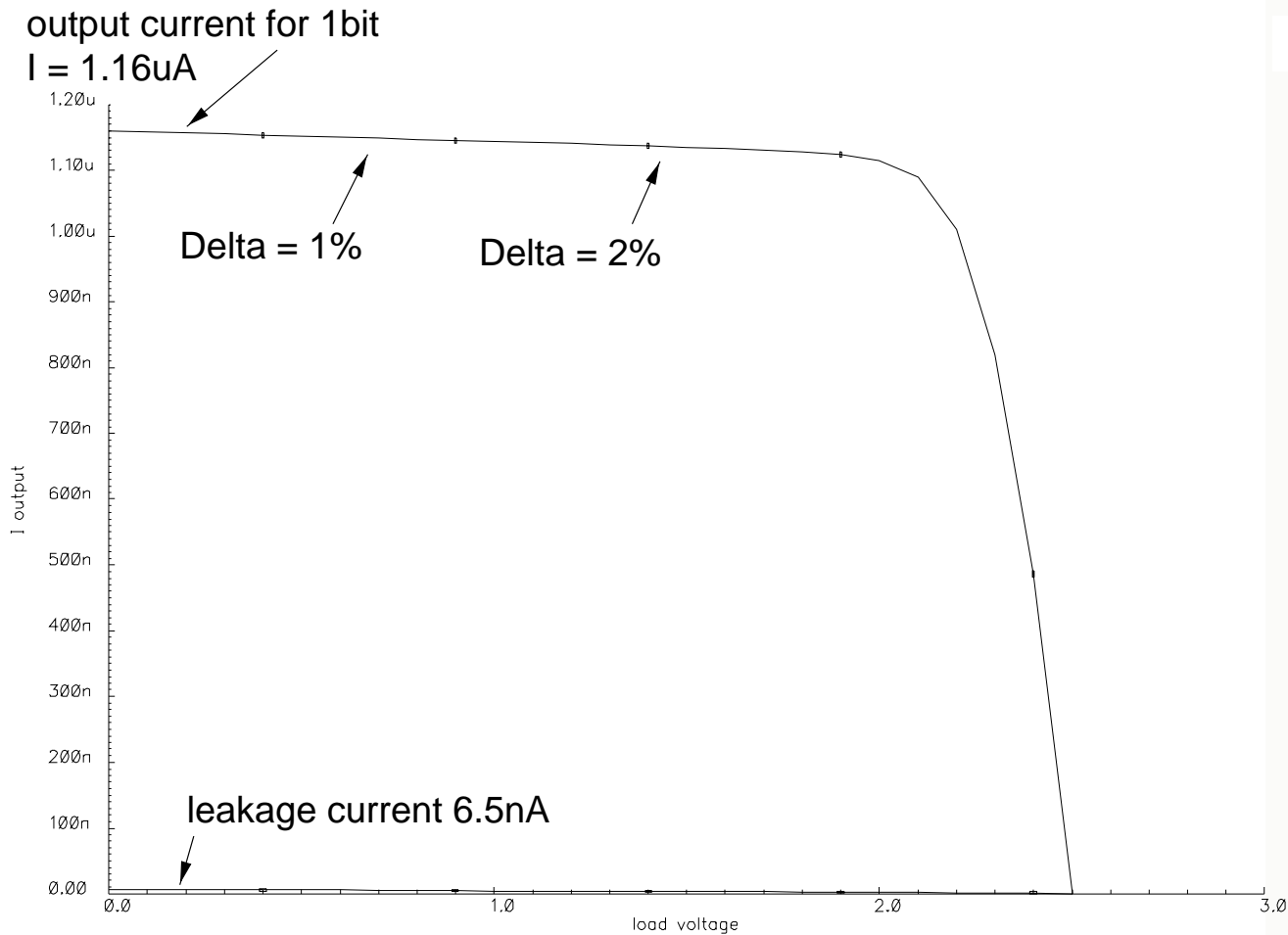
BeetleBG-1.0

- 3 different types of current sources
- 10bit R2R ladder voltage DAC
- 10 bit current DAC
- teststructures to study transistor parameters under irradiation

to be bonded to the FE chip

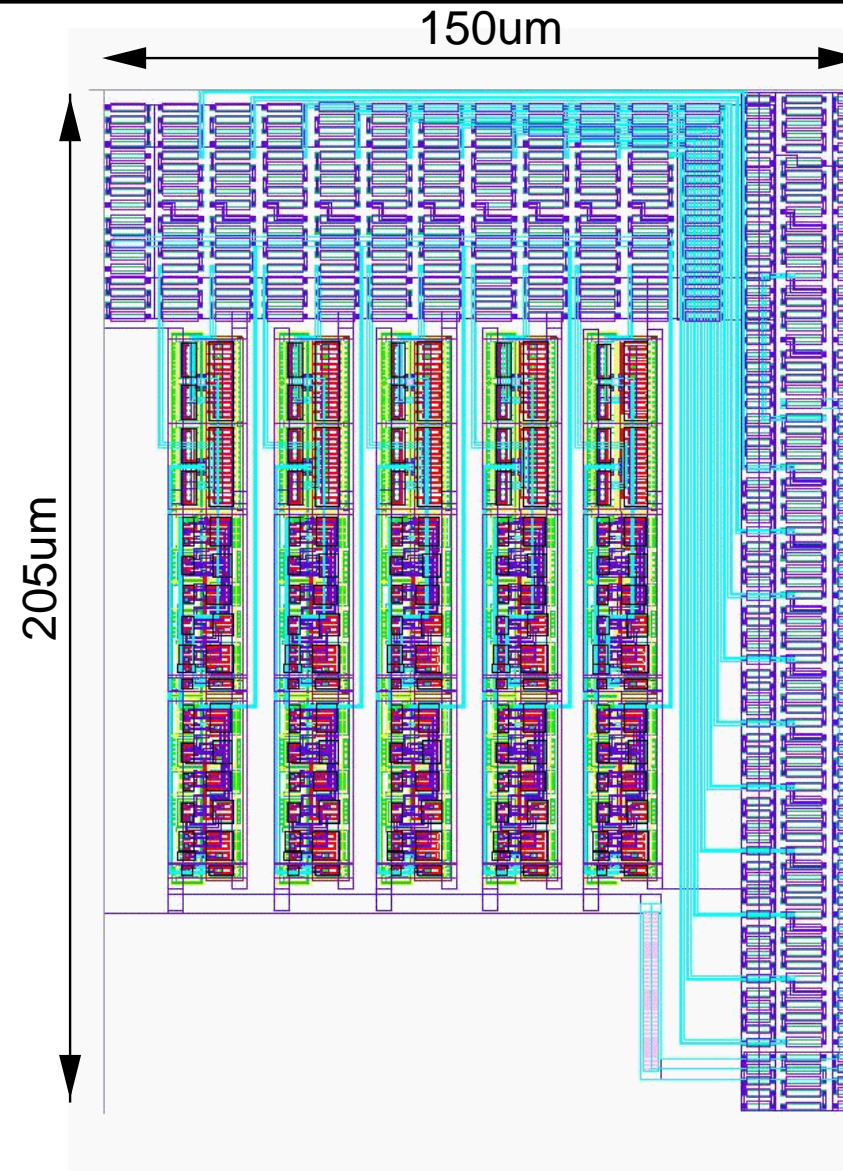
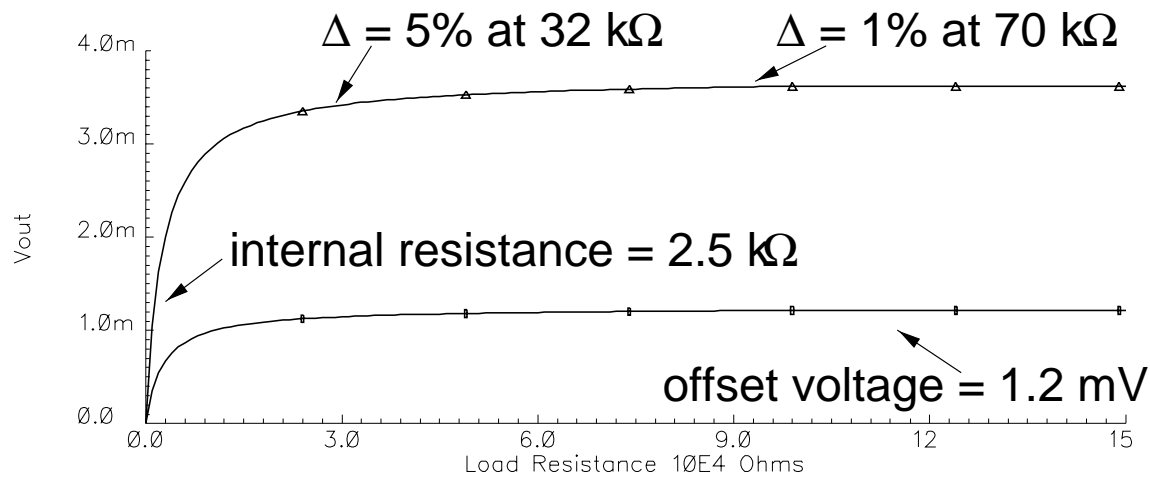
current DAC with a resolution of 10 bit

- 1024 conventional pmos
W/L = 0.6 μm / 3 μm
- 132 dummy pmos for matching



R2R voltage DAC with a resolution of 10bit

- 34 N+ diffusion resistors each $3.0\text{k}\Omega$
- output range 0 to 2.5 V
- power consumption 690 μW



3 different types of current sources

type of current source	maximum load ($\Delta I = 1\%$)	small signal resistance	power	size
100 uA current source with opamp feedback	1.06 V	4 M Ω	2.35 mW	164 x 61 μm^2
100 uA current source with opamp feedback and regular cascode output	1.94 V	14 M Ω	2.5 mW	189 x 61 μm^2
100 uA regular cascode	1.93 V	17 M Ω	599 μW	84 x 23 μm^2

future milestones:

- end of '99: submission of further components
 - second iteration of frontend
 - calibration pulse generator
 - comparator
 - pipeline capacitor array
 - pipeline readout amplifier
 - control logic
 - multiplexer
 - readout buffer

- october 2000: first iteration of readout chip
- october 2001: final readout chip

(plus additional test runs)

see status on: <http://wwwasic.ihep.uni-heidelberg.de/lhcb>